

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Miyoko SHIMADA, et al.

Serial No.: 09/982,003

Filed: October 19, 2001

For: METHOD OF MANUFACTURING
SEMICONDUCTOR DEVICE

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) Group Art Unit: 2829
)
) Examiner: Kilday, Lisa A.
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Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

TRANSMITTAL LETTER

Enclosed is a reply to the Final Office Action of February 21, 2003. The items checked below are appropriate:

- ☐ Applicants hereby petition for a month extension of time to respond to the above Office Action. The fee of \$ for the Extension is enclosed.

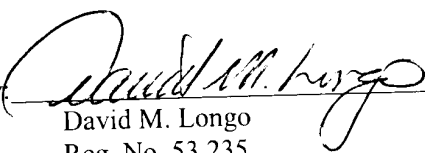
The claims are calculated below:

	Claims Remaining After Amendment		Highest Number Previously Paid	Present Extra	Rate	Additional Fee
Total	26	-	20	6	x \$ 18	\$ 108.00
Indep.	2	-	3	0	x \$ 84	0.00
<input type="checkbox"/> First Presentation of Multiple Dep. Claim(s)					+\$280	0.00
Subtotal						\$ 108.00
Reduction by 1/2 if small entity						- 0.00
TOTAL						\$ 108.00

- ☐ A fee of \$108 to cover the cost of the additional claims added by this reply is enclosed.
- ☐ A fee of \$750 to cover the Request for Continued Examination (RCE) is enclosed.
- ☐ A check for \$858 to cover the above fees is enclosed.

Please grant any extensions of time required to enter this response and charge any additional required fees to our deposit account 06-0916.

Dated: May 21, 2003

By 
David M. Longo
Reg. No. 53,235

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C. PATENT
Customer No. 22,852
Attorney Docket No. 04329.2688

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Sir:

AMENDMENT

In reply to the Final Office Action of February 21, 2003, and in support of the RCE filed concurrently herewith, please amend the application as follows:

IN THE CLAIMS:

Please cancel claims 15, 17, and 19 without prejudice or disclaimer of their subject matter, amend claims 1, 2, and 4 – 7, and add new claims 20 – 29 as follows.

1. (Twice Amended) A method of manufacturing a semiconductor device comprising:
preparing a substrate to be treated; and

forming an insulation film above the substrate, which includes applying an insulation film raw material above the substrate, the insulation film raw material including a substance or a precursor of the substance, the insulation film comprising the substance, curing the insulation

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